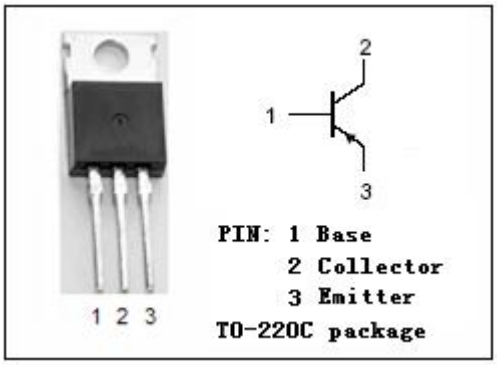
isc Silicon PNP Power Transistor — 2SB983

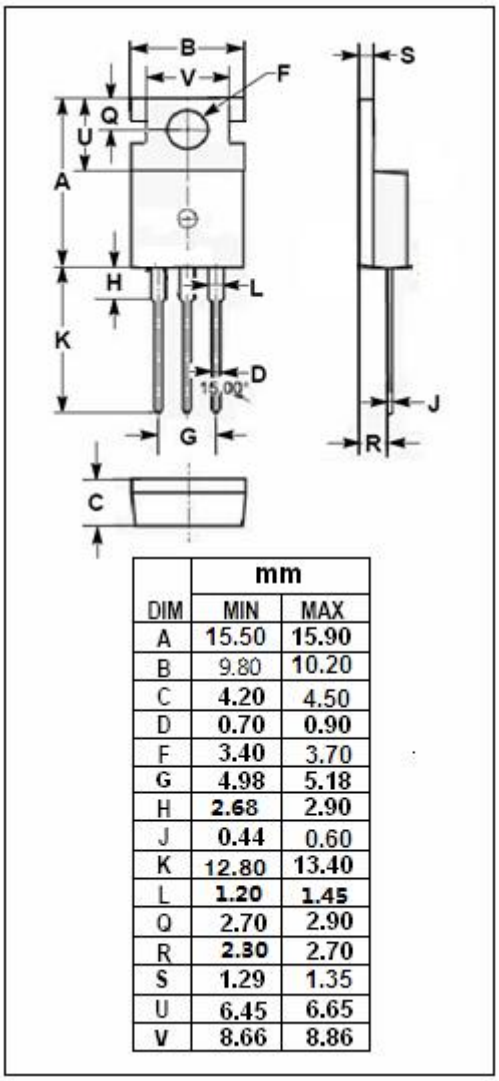
DESCRIPTION

- High Switching Time
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= -0.4V(Max)@I_C= -4A
- Wide Area of Safe Operation
- Complement to Type 2SD1345
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Inverters, converters
- Controllers for DC motor, pulse motor
- Switching power supplies
- General power applications



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-7	A
I_{CM}	Collector Current-Peak	-12	A
I_B	Base Current-Continuous	-1.5	A
I_{BM}	Base Current-Peak	-4	A
P_C	Total Power Dissipation @ T_C=25℃	40	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.1	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; I_B= 0	-50			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -0.4A			-0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -4A; I_B= -0.4A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= -40V; I_B= 0			-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-0.1	mA
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -2V	70		200	